

Silicon PNP Power Transistors

2SB653

DESCRIPTION

- With TO-3 package
- High power dissipation

APPLICATIONS

- For low frequency power amplifier applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector



Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings($T_a = \square$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-120	V
V_{CEO}	Collector-emitter voltage	Open base	-120	V
V_{EBO}	Emitter-base voltage	Open collector	-6	V
I_C	Collector current		-7	A
P_C	Collector power dissipation	$T_C = 25\square$	60	W
T_j	Junction temperature		150	$\square$
T_{stg}	Storage temperature		-55~150	$\square$

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C = -30\text{mA}$; $I_B = 0$	-120			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C = -1\text{mA}$; $I_E = 0$	-120			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E = -1\text{mA}$; $I_C = 0$	-6			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C = -3\text{A}$; $I_B = -0.3\text{A}$			-1.5	V
I_{CBO}	Collector cut-off current	$V_{CB} = -120\text{V}$; $I_E = 0$			-0.1	mA
I_{EBO}	Emitter cut-off current	$V_{EB} = -6\text{V}$; $I_C = 0$			-0.1	mA
h_{FE}	DC current gain	$I_C = -1\text{A}$; $V_{CE} = -5\text{V}$	35		200	
f_T	Transition frequency	$I_C = -1\text{A}$; $V_{CE} = -5\text{V}$		20		MHz

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PACKAGE OUTLINE

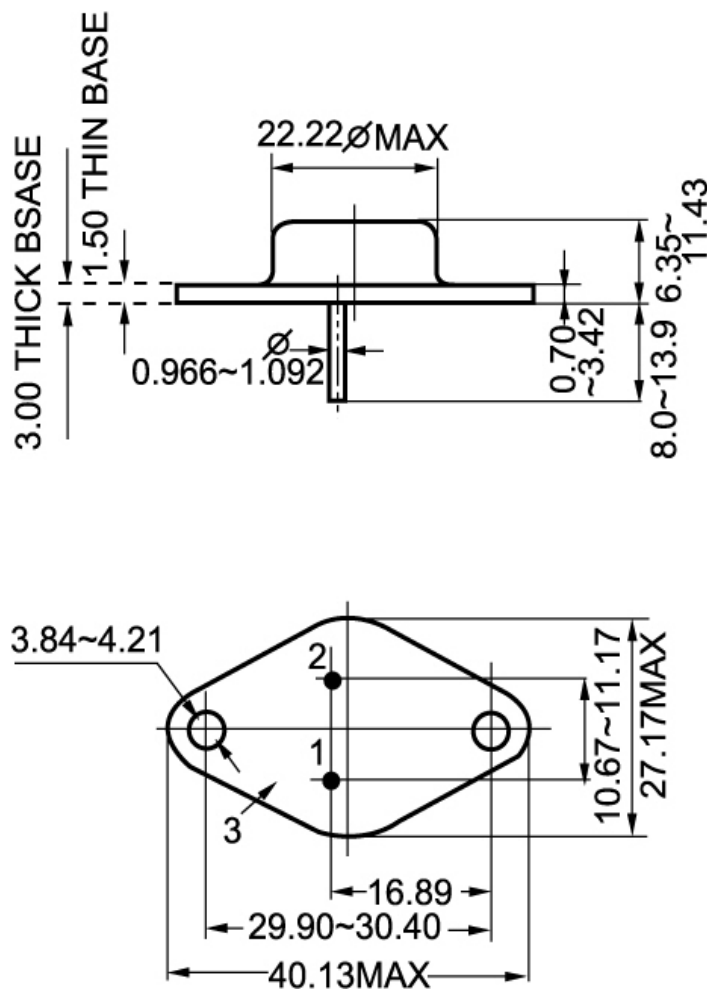


Fig.2 outline dimensions (unindicated tolerance:±0.1mm)